Hi-Reliability RAD Capable Optoisolator

HCC1002



Features:

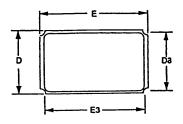
- TID Capable to 100Krad (SI)/cm2 ELDRS (0.1rad/s)
- Neutron capable to 1E12 neutrons (14MeV)
- TX & TXV Processing available to MIL-STD-19500
- 1 KV electrical Isolation

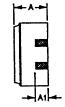
Description:

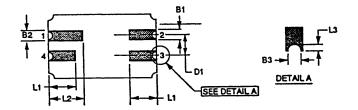
This device is similar to Optek's 4N series of optoisolators with exception of the die. TX & TXV processing is per MIL-PRF-19500 and can be modified per customer SCDs. Each device consists of a IRLED & NPN transistor mounted in a hermetic 4 pin LCC SMD.

Applications:

Circuit electrical isolation in space applications such as satellites, launchers, space vehicles and planetary rovers



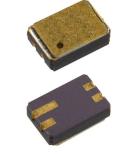




Dimensions					
	Inc	hes	Millimeters		
Ltr	Min	Max	Min	Max	
А	.061	.075	1.55	1.90	
A1	.026	.034	0.66	0.88	
B1	.022	.028	0.56	0.71	
B2	.072	Ref	1.83 Ref		
B3	.006	.022	0.15	0.56	
D	.145	.155	3.68 1.14 -	3.93	
D1	.045	.055		1.39	
D3	-	.155		3.93	
E	.215	.225	5.46	5.71	
E3	-	.225	-	5.71	
L1	.032	.048	0.81	1.22	
L2	.072	.088	1.83	2.23	
L3	.003	.007	0.08	0.18	
N	4				
ND	2				
NE	()			

General Note

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range	-55° C to +150° C
Operating Temperature Range	-55° C to +150° C
Input-to-Output Isolation Voltage	± 1.00 kVDC ⁽¹⁾
Lead Soldering Temperature (TO-78 Metal Can) [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽²⁾
Soldering Temperature (SMD) Vapor Phase Reflow for 30 seconds	215° C

Input Diode (LED)

Forward DC Current (65° C or below)	40 mA
Reverse Voltage	2 V
Power Dissipation	60 mW ⁽³⁾

Output Phototransistor:

Continuous Collector Current	50 mA
Collector-Emitter Voltage	40 V
Power Dissipation	300 mW ⁽⁴⁾

Notes:

- 1. Measured with input leads shorted together and output leads shorted together.
- 2. RMA flux is recommended.
- 3. Derate linearly 1.0 mW/° C above 65° C.
- 4. Derate linearly 3.0 mW/° C above 25° C.

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Performance

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS
Input Dioc	le	•		-		
V _F	Forward Voltage	0.80 1.00 0.70	- - -	1.70 1.9 1.50	V	I _F = 10.0 mA I _F = 10.0 mA, T _A = -55° C I _F = 10.0 mA, T _A = 125° C
I _R	Reverse Current	-	-	100	μA	V _R = 2.0 V
Output Ph	ototransistor					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	40	-	-	V	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0, I_{\rm F} = 0$
V _{(BR)EBO}	Emitter-Collector Breakdown Voltage	7	-	-	V	$I_E = 100 \ \mu\text{A}, I_C = 0, I_F = 0$
${\sf I}_{\sf C(\sf OFF)}^1$	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 20 V, I _B = 0, I _F = 0
I _{C(OFF)} ²	Collector-Emitter Dark Current	-	-	100	μA	$V_{CE} = 20 \text{ V}, \text{ I}_{B} = 0, \text{ I}_{F} = 0, \text{ T}_{A} = 100^{\circ} \text{ C}$
Coupled						
I _{C(ON)}	On-State Collector Current	1 15 10 15 2.8 2.0			mA	$\begin{split} I_F &= 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}, I_B = 0 \\ I_F &= 15.0 \text{ mA}, V_{CE} = 1.0 \text{ V}, I_B = 0 \\ I_F &= 10.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0 \\ I_F &= 15.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0 \\ I_F &= 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = -55^\circ \text{ C} \\ I_F &= 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_B = 0, T_A = 100^\circ \text{ C} \end{split}$
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.30	v	I _F = 20.0 mA, I _C = 10.0 mA, I _B = 0
R _{IO}	Resistance (Input-to-Output)	10 ¹¹	-	-	Ω	$V_{I-O} = \pm 1000 \text{ VDC}^{(1)}$
C _{IO}	Capacitance (Input-to-Output)	-	-	5	pF	V _{I-O} = 0 V, f = 1.0 MHz ⁽¹⁾
T _{r,} T _f	Rise and Fall Time	-	-	20	μs	V_{CC} = 10.0 V , I_F = 10.0 mA, R_L = 100 Ω

Notes:

1. Measured with input leads shorted together and output leads shorted together.

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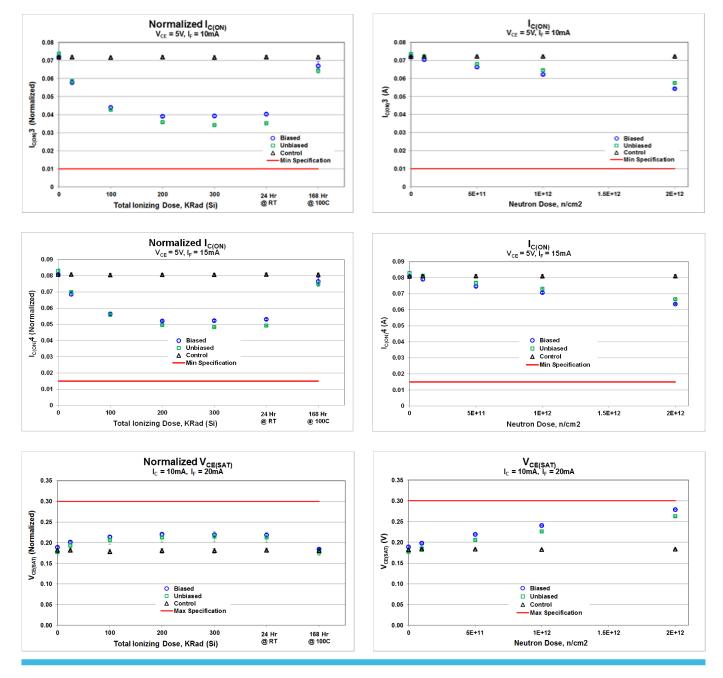
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Radiation Test Standards

- Total Ionizing Dose: MIL-STD-883 Method 1019.7 and ASTM F1892-06 (0.1rad (si)/s) dose rate
- Neutron: MIL-STD-883 Method1017.2 and ASTM Designation: E 772-94
- Full Radiation report available



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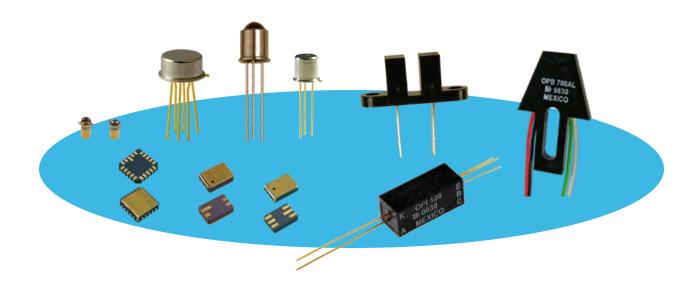
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Packaging

Package styles available:

Radiation testing was in a TO-78 can; functional & radiation samples can be supplied in discrete pairs such as, "pills" or TO-46 / TO-18 metal cans, 4 & 6 pin Hermetic Ceramic LLC, high voltage assemblies like the OPI120 and OPI150 hermetic high voltage isolators and more.



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Issue	Change Description	Approval	Date
А	Initial Preliminary Release	R. Bailey	3-23-16
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